

MOSFETs Silicon N-channel MOS (U-MOS<sup>Ⅷ</sup>-H)

# TK100A06N1

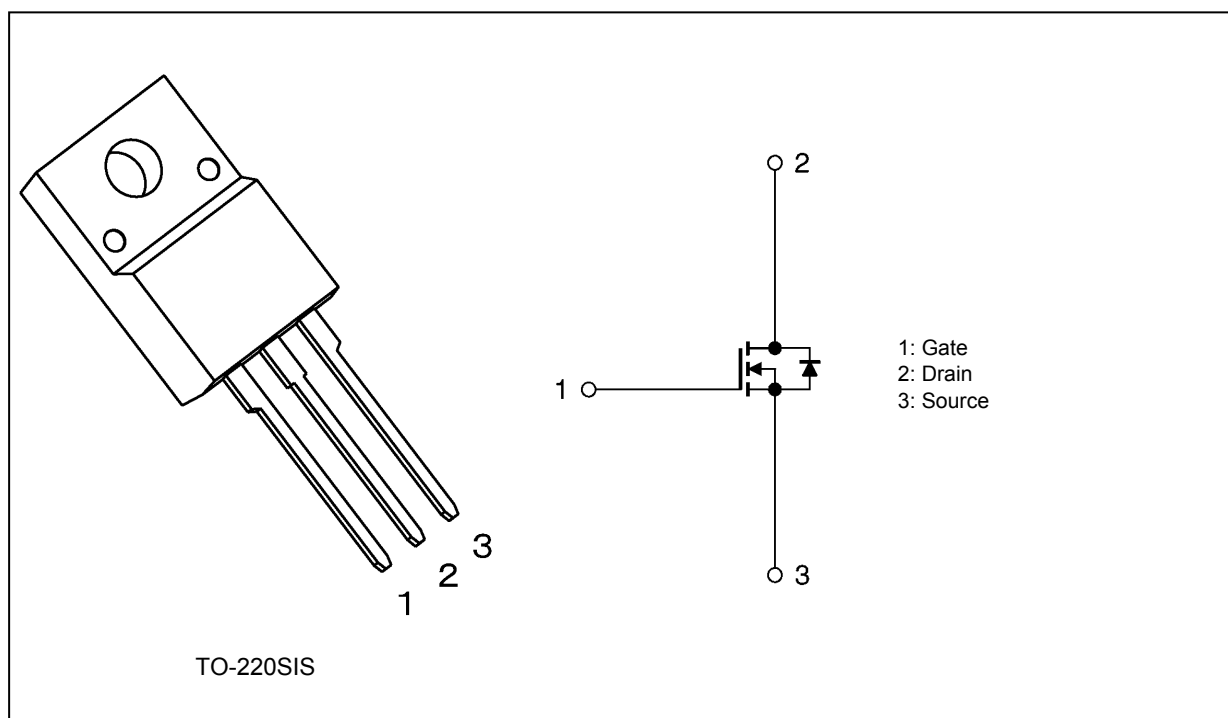
## 1. Applications

- Switching Voltage Regulators

## 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 2.2 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (2) Low leakage current:  $I_{DSS} = 10 \text{ }\mu\text{A}$  (max) ( $V_{DS} = 60 \text{ V}$ )
- (3) Enhancement mode:  $V_{th} = 2.0 \text{ to } 4.0 \text{ V}$  ( $V_{DS} = 10 \text{ V}$ ,  $I_D = 1.0 \text{ mA}$ )

## 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	$V_{\text{DSS}}$	60	V
Gate-source voltage	$V_{\text{GSS}}$	$\pm 20$	
Drain current (DC) (Silicon limit) (Note 1), (Note 2)	$I_{\text{D}}$	263	A
Drain current (DC) ( $T_c = 25^\circ\text{C}$ ) (Note 1)	$I_{\text{D}}$	100	
Drain current (pulsed) ( $t = 1 \text{ ms}$ ) (Note 1)	$I_{\text{DP}}$	584	
Power dissipation ( $T_c = 25^\circ\text{C}$ )	$P_{\text{D}}$	45	W
Single-pulse avalanche energy (Note 3)	$E_{\text{AS}}$	413	mJ
Avalanche current	$I_{\text{AR}}$	100	A
Channel temperature	$T_{\text{ch}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{\text{th(ch-c)}}$	2.77	$^\circ\text{C/W}$
Channel-to-ambient thermal resistance	$R_{\text{th(ch-a)}}$	62.5	

Note 1: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 2: Limited by silicon chip capability. Package limit is 100A.

Note 3:  $V_{\text{DD}} = 48 \text{ V}$ ,  $T_{\text{ch}} = 25^\circ\text{C}$  (initial),  $L = 31.8 \mu\text{H}$ ,  $I_{\text{AR}} = 100 \text{ A}$

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

## 6. Electrical Characteristics

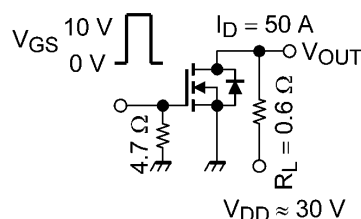
### 6.1. Static Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$	—	—	$\pm 0.1$	$\mu\text{A}$
Drain cut-off current	$I_{DSS}$	$V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$	—	—	10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 10\text{ mA}$ , $V_{GS} = 0\text{ V}$	60	—	—	V
Drain-source breakdown voltage (Note 4)	$V_{(BR)DSX}$	$I_D = 10\text{ mA}$ , $V_{GS} = -20\text{ V}$	45	—	—	
Gate threshold voltage	$V_{th}$	$V_{DS} = 10\text{ V}$ , $I_D = 1.0\text{ mA}$	2.0	—	4.0	
Drain-source on-resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}$ , $I_D = 50\text{ A}$	—	2.2	2.7	$\text{m}\Omega$

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

### 6.2. Dynamic Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	$C_{iss}$	$V_{DS} = 30\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$	—	10500	—	$\text{pF}$
Reverse transfer capacitance	$C_{rss}$		—	50	—	
Output capacitance	$C_{oss}$		—	3500	—	
Gate resistance	$r_g$	—	—	3.0	—	$\Omega$
Switching time (rise time)	$t_r$	See Figure 6.2.1.	—	67	—	ns
Switching time (turn-on time)	$t_{on}$		—	110	—	
Switching time (fall time)	$t_f$		—	64	—	
Switching time (turn-off time)	$t_{off}$		—	180	—	



Duty  $\leq 1\%$ ,  $t_w = 10\text{ }\mu\text{s}$

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 48\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_D = 100\text{ A}$	—	140	—	nC
Gate-source charge 1	$Q_{gs1}$		—	44	—	
Gate-drain charge	$Q_{gd}$		—	38	—	
Gate switch charge	$Q_{SW}$		—	56	—	

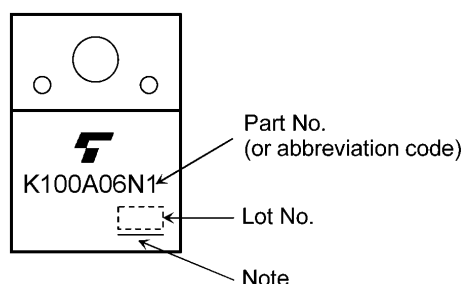
#### 6.4. Source-Drain Characteristics ( $T_a = 25^\circ\text{C}$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 5)	$I_{DR}$	—	—	—	100	A
Reverse drain current (pulsed) (Note 5)	$I_{DRP}$		—	—	584	
Diode forward voltage	$V_{DSF}$	$I_{DR} = 100\text{ A}, V_{GS} = 0\text{ V}$	—	—	-1.2	V
Reverse recovery time (Note 6)	$t_{rr}$	$I_{DR} = 100\text{ A}, V_{GS} = 0\text{ V}$ $-di_{DR}/dt = 100\text{ A}/\mu\text{s}$	—	100	—	ns
Reverse recovery charge (Note 6)	$Q_{rr}$		—	220	—	nC

Note 5: Ensure that the channel temperature does not exceed  $150^\circ\text{C}$ .

Note 6: Ensure that  $V_{DS}$  peak does not exceed  $V_{DSS}$ .

#### 7. Marking (Note)



**Fig. 7.1 Marking**

Note: A line under a Lot No. identifies the indication of product Labels.

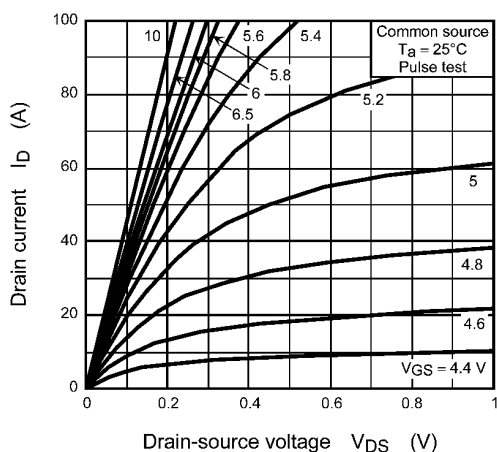
Not underlined:  $[[Pb]]/INCLUDES > MCV$

Underlined:  $[[G]]/RoHS\ COMPATIBLE$  or  $[[G]]/RoHS\ [[Pb]]$

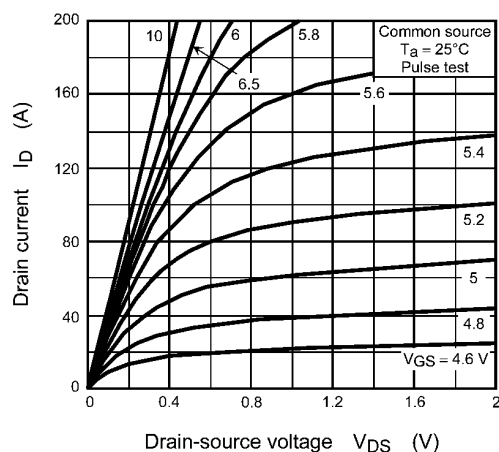
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

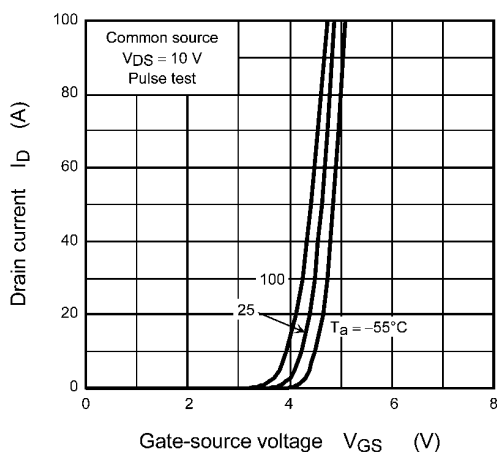
# 8. Characteristics Curves (Note)



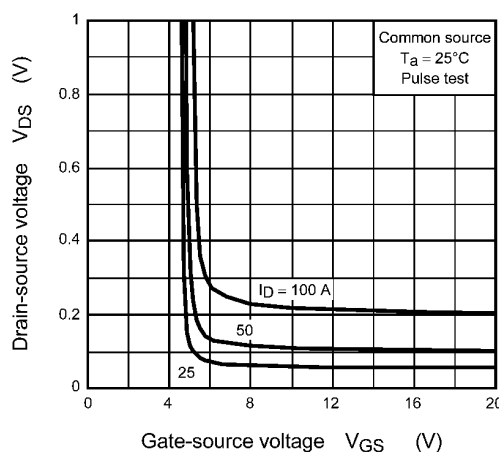
**Fig. 8.1  $I_D - V_{DS}$**



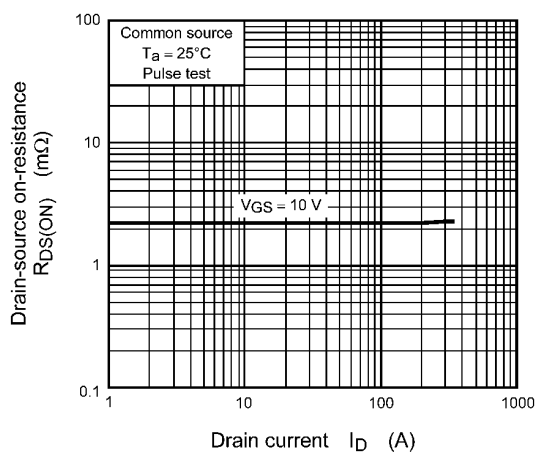
**Fig. 8.2  $I_D - V_{DS}$**



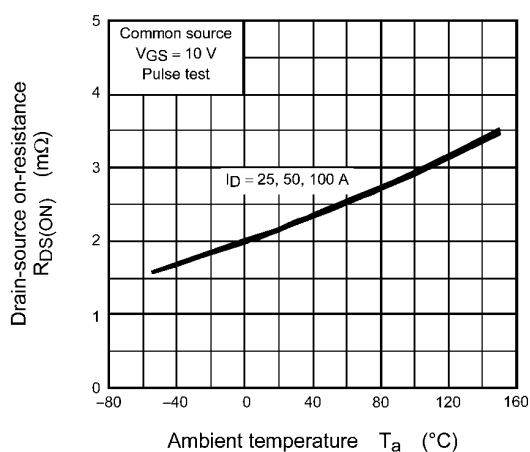
**Fig. 8.3  $I_D - V_{GS}$**



**Fig. 8.4  $V_{DS} - V_{GS}$**



**Fig. 8.5  $R_{DS(ON)} - I_D$**



**Fig. 8.6  $R_{DS(ON)} - T_a$**

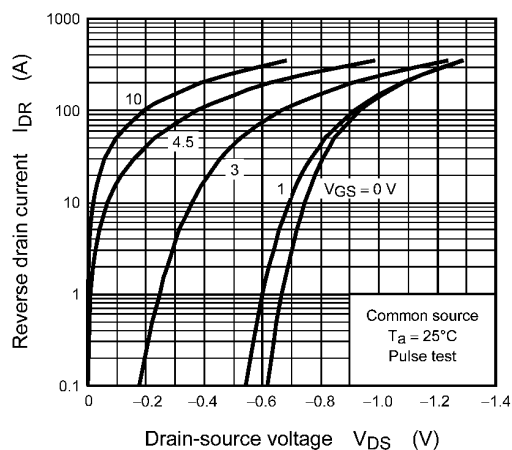


Fig. 8.7  $I_{DR} - V_{DS}$

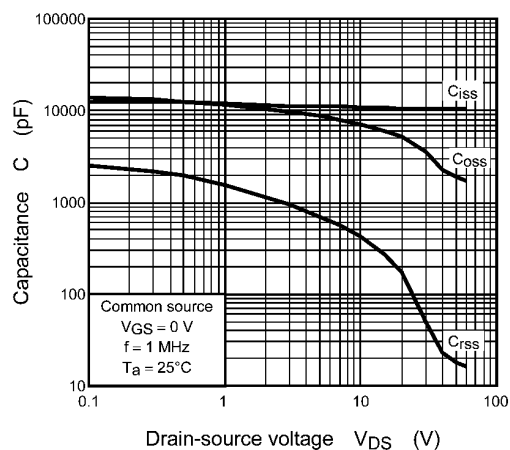


Fig. 8.8 Capacitance -  $V_{DS}$

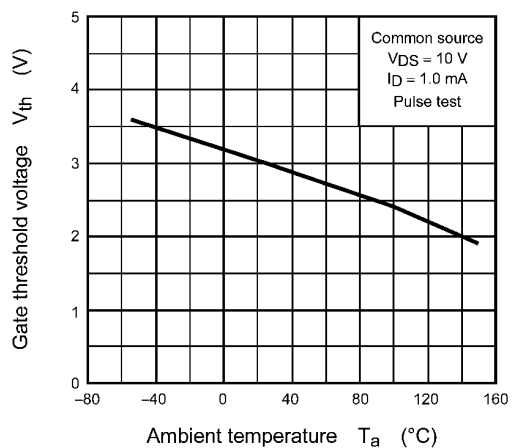


Fig. 8.9  $V_{th} - T_a$

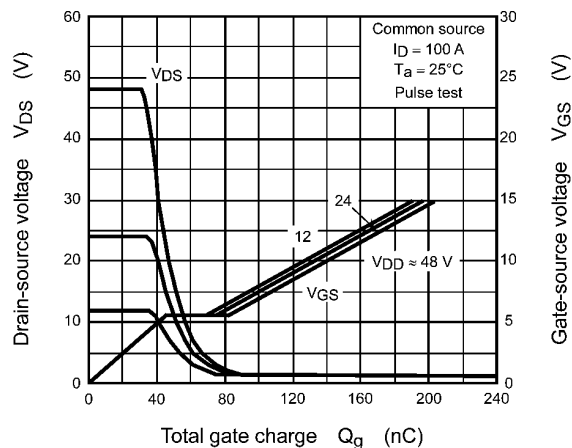


Fig. 8.10 Dynamic Input/Output Characteristics

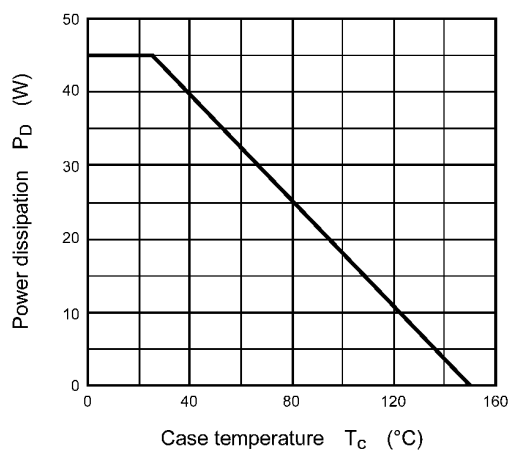
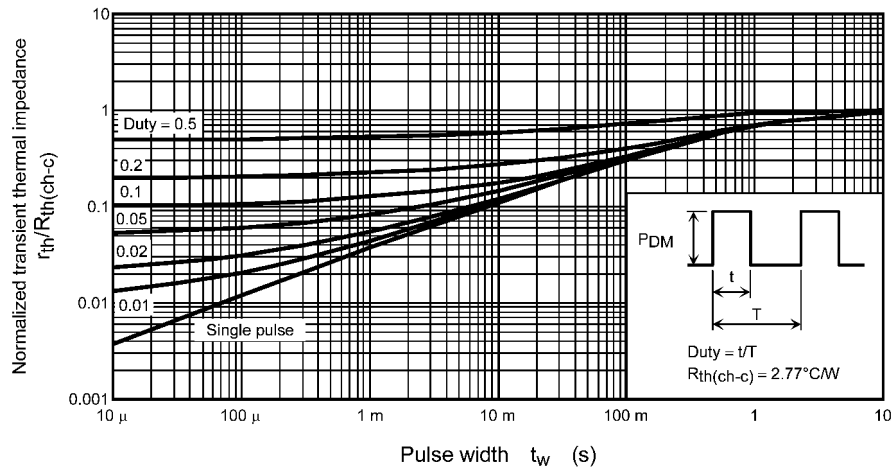
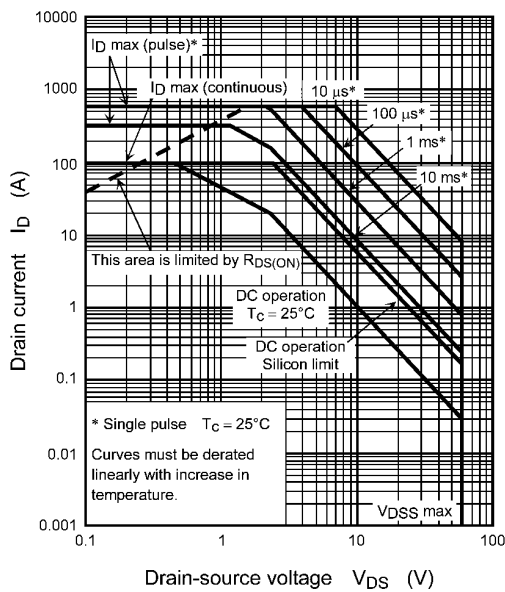


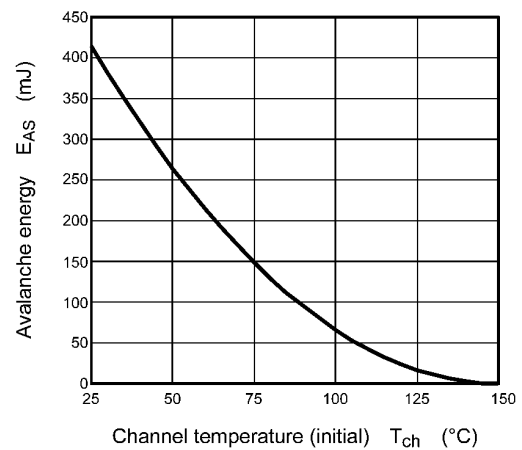
Fig. 8.11  $P_D - T_c$   
 (Guaranteed Maximum)



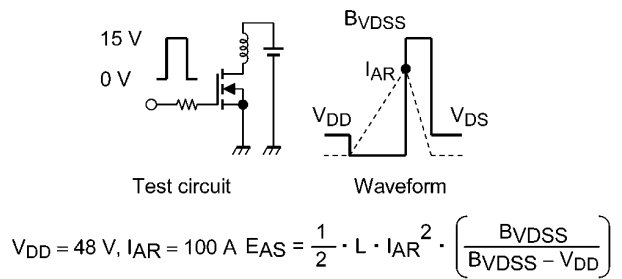
**Fig. 8.12  $r_{th}/R_{th(ch-c)} - t_w$**   
(Guaranteed Maximum)



**Fig. 8.13 Safe Operating Area**  
(Guaranteed Maximum)



**Fig. 8.14  $E_{AS} - T_{ch}$**   
(Guaranteed Maximum)



**Fig. 8.15 Test Circuit/Waveform**

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

Package Name(s)
JEITA: SC-67
TOSHIBA: 2-10U1S
Nickname: TO-220SIS



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**Телефон:** +7 812 627 14 35

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**Адрес:** 198099, Санкт-Петербург,  
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